

In the Claims:

1. (Currently Amended) A method of manufacturing a module, the method comprising:
providing a device that includes a connection area extending over a top surface of the device,
wherein the connection area comprises a compliant 3D structure that includes a conductor overlying
a compliant base element, the conductor being integral with a redistribution layer that overlies the
device;
applying a casting compound over the top surface of the device;
after applying a casting compound, reducing a thickness of the casting compound so that the
connection area protrudes through the casting compound;~~and~~
~~after applying a casting compound, electrically coupling the connection area to a terminal of
a second apparatus.~~
2. (Currently Amended) The method of claim 1 ~~wherein the second apparatus comprises a
printed circuit board, the method~~ further comprising, after applying the casting compound, mounting
the module to the printed circuit board.
3. (Currently Amended) The method of claim 1 ~~wherein the second apparatus comprises a lead
frame, the method~~ further comprising, after forming the casting compound, attaching the module to
the lead frame.
4. (Currently Amended) The method of ~~claim 1~~ claim 26 wherein electrically coupling the
connection area comprises soldering the connection area to the terminal.
5. (Canceled)

6. (Canceled)
7. (Original) The method of claim 1 wherein the device comprises a semiconductor wafer.
8. (Original) The method of claim 7 and further comprising separating the wafer into a plurality of individual chips, wherein the casting compound is applied to the wafer before the separating.
9. (Original) The method of claim 8 wherein separation corridors between the chips on the wafer are exposed before the separating.
10. (Original) The method of claim 9 wherein the separation corridors are exposed by a photolithographic process.
11. (Original) The method of claim 9 wherein the separation corridors are exposed with use of a laser beam.
12. (Original) The method of claim 8 wherein the wafer is cooled to a temperature at which the casting compound is adequately brittle before separating the wafer into a plurality of individual chips.
13. (Original) The method of claim 1 wherein the casting compound is applied uniformly by spraying, dispensing or printing.
14. (Original) The method of claim 1 wherein the casting compound has thermal and mechanical properties comparable to those of silicon.

15. (Original) The method of claim 14 wherein the casting compound comprises a silicon-based material.

16. (Original) The method of claim 14 wherein the casting compound comprises a thermoplastic material.

17. (Original) The method of claim 14 wherein the casting compound comprises an epoxy resin.

18. (Canceled)

19. (Previously Presented) The method of claim 1 wherein the thickness of the casting compound is reduced by thermal removal.

20. (Previously Presented) The method of claim 1 wherein the thickness of the casting compound is reduced by etching.

21. (Currently Amended) A method for improving the mechanical properties of a BOC module arrangement in which chips have 3D structures which are mechanically and electrically connected by means of solder connections to terminal contacts on a printed circuit board or leadframe, the method characterized in that a casting compound is applied over ~~[[the]]~~ a top surface of the chips ~~device~~, and excess thickness of the casting compound is removed, in such a way that tips of the 3D structures protrude from the compound, wherein the 3D structures comprise compliant 3D structures each of which includes a conductor overlying a compliant base element, the conductor being integral with a redistribution layer that overlies the top surface of the chips.

22. (Canceled)

23. (Currently Amended) The method of claim 21 wherein the ~~compliant 3D structure~~
~~comprises a compliant base element, on which an electrically conductive structure of~~ conductor
comprises metal is applied.

24. (Original) The method of claim 21 wherein the chips comprise a plurality of chips on a semiconductor wafer.

25. (Original) The method of claim 21 wherein the chips comprise individual semiconductor dies.

26. (New) The method of claim 1, further comprising, after applying a casting compound, electrically coupling the connection area to a terminal of a second apparatus.

27. (New) The method of claim 8, wherein separating the wafer into a plurality of individual chips comprises using a laser to separate the wafer.